ABSTRACT OF THE DISCLOSURE

A cleaning gas which is employed to remove an unnecessary deposited material formed in a thin film forming apparatus by thermal decomposition of pentaethoxytantalum or tetraethoxysilane without damaging a reactor, tools, parts and piping of a silicon oxide film-forming apparatus or a tantalum oxide film-forming apparatus. The cleaning gas comprises HF gas and at least one of an oxygen-containing gas, a fluorine gas, a chlorine fluoride gas, a bromine fluoride gas and an iodine fluoride gas.

This Sheet Has Been Replaced

